Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics

Direct Laser Lithography of Asymmetric Graphene Ribbons on a Polydimethylsiloxane Trench Structure —Supplementary Information

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This file includes:

SUPPLEMENTARY FIG. S1-S2

SUPPLEMENTARY FIGURES AND CAPTIONS

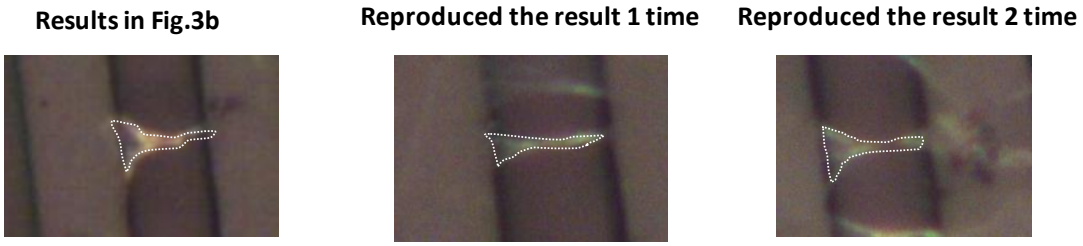

Figure S1 | The reproducibility of direct laser lithography of asymmetric graphene ribbons. The results showing that the triangular shaped structures could be reproduced for multi-times.

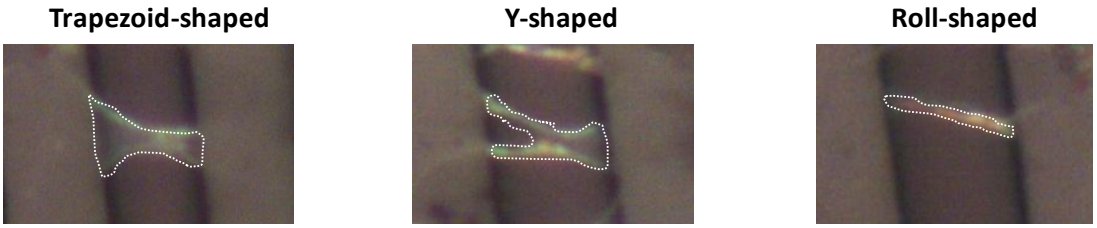

Figure S2 | The flexibility of direct laser lithography of asymmetric graphene ribbons. The results showing that the trapezoid-shaped, Y-shaped and roll-shaped could also be fabricated.